

Radar Pulsed Power Transistor 6W, 1.2-1.4 GHz, 100µs Pulse, 10% Duty

M/A-COM Products Released, 30 May 07

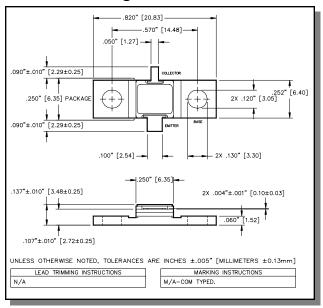
Features

- · NPN silicon microwave power transistors
- · Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- · Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- · Hermetic metal/ceramic package
- RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	65	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	Ι _C	1.5	Α
Power Dissipation @ +25°C	P _{TOT}	30	W
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 12mA		BV _{CES}	65	-	V
Collector-Emitter Leakage Current	V _{CE} = 40V		I _{CES}	-	1.5	mA
Thermal Resistance	Vcc = 28V, Pin = 1.2W	F = 1.2, 1.3, 1.4 GHz	R _{TH(JC)}	-	5.8	°C/W
Output Power	Vcc = 28V, Pin = 1.2W	F = 1.2, 1.3, 1.4 GHz	P _{OUT}	6.0	-	W
Power Gain	Vcc = 28V, Pin = 1.2W	F = 1.2, 1.3, 1.4 GHz	G _P	7.0	-	dB
Collector Efficiency	Vcc = 28V, Pin = 1.2W	F = 1.2, 1.3, 1.4 GHz	ης	45	-	%
Input Return Loss	Vcc = 28V, Pin = 1.2W	F = 1.2, 1.3, 1.4 GHz	RL	-	-6	dB
Load Mismatch Tolerance	Vcc = 28V, Pin = 1.2W	F = 1.2, 1.3, 1.4 GHz	VSWR-T	-	3:1	-
Load Mismatch Stability	Vcc = 28V, Pin = 1.2W	F = 1.2, 1.3, 1.4 GHz	VSWR-S	-	1.5:1	-

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

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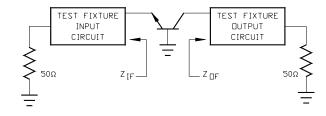
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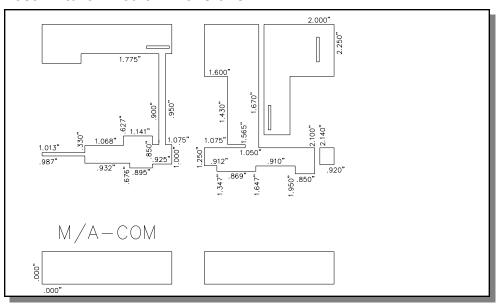
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RF Test Fixture Impedance

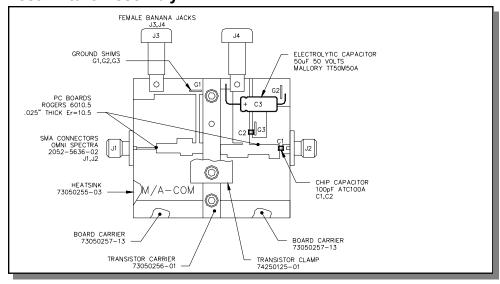
F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
1.2	TBD	TBD
1.3	TBD	TBD
1.4	TBD	TBD



Test Fixture Circuit Dimensions



Test Fixture Assembly



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